

US1A THRU US1K

Technical Data Data Sheet N2018, Rev. -



US1A THRU US1K SURFACE MOUNT ULTRA FAST RECTIFIER



Features

- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Material has UL Classification 94V-O
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.06 grams(approx)

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	US1A	US1B	US1D	US1G	US1J	US1K	Units	
Peak Repetitive Reverse Voltage	VRRM	50	100	200	400	600	800	_ v	
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560		
Average Rectified Output Current @T∟=100°C	lo				1.0			Α	
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}				35			А	
Rating for fusing (t<8.3ms)		5.08				A ² s			
Forward voltage @IF =1.0A	VF		1.0		1.3	1.	.7	V	
ak Reverse Current $@T_A = 25^{\circ}C$ 5Rated DC Blocking Voltage $@T_A = 125^{\circ}C$ IR200			μA						
Typical junction capacitance (Note 2)		45.0				pF			
Reverse Recovery Time (Note 1)	Trr	50		7	5	ns			
bical thermal resistance (Note 3) R _{0JA} 30			°C/W						
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to +150		°C					

* Pulse width < 300 μ s, duty cycle < 2%

Note: 1.Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A.

2. Measured at 1.0 MHz and Applied reverse Voltage of 4.0V D.C

3. 8.0mm² (.13mm Thick) Land Areas.

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Circuit Diagram





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RoHS 🗭

Ratings and Characteristics Curves

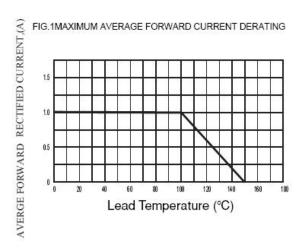
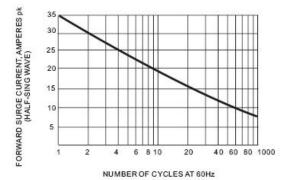
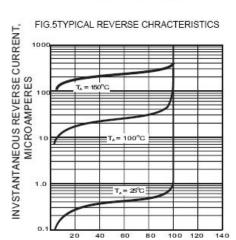
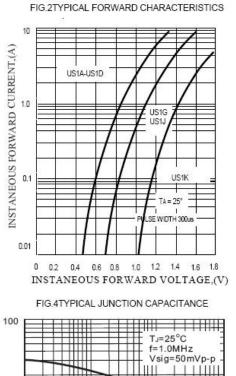


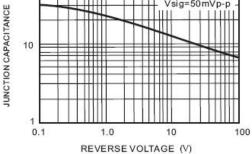
FIG.3MAXIMUM NON-REPEITIVE SURGE CURRENT



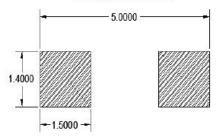


PERCENT OF RATED PEAK INVERSE VOLTGE





SMA PAD LAYOUT



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(PF)

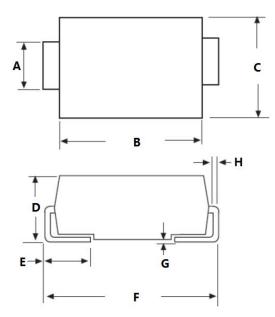


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Mechanical Dimensions SMA (Inches/Millimeters)



	mechanical size (mm)				
Item	MIN	MAX	MIN	MAX	
А	1.25	1.65	0.049	0.065	
В	3.95	4.6	0.156	0.181	
С	2.25	2.95	0.089	0.116	
D	1.95	2.9	0.077	0.114	
E	0.75	1.6	0.03	0.063	
F	4.8	5.6	0.189	0.22	
G	0.05	0.2	0.002	0.008	
Н	0.15	0.41	0.006	0.016	

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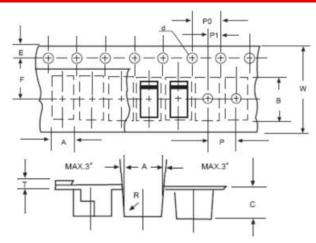
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Ordering Information

Device	Package	Shipping
US1A		
THRU	SMA (Pb-Free)	5000pcs / reel
US1K	. ,	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Carrier Tape Specification SMA



Ч	US1A	Ь
4	XXXXX	μ

Marking Diagram

Where XXXXX is YYWWL

= Device Type = Forward Current (1A)

= Reverse Voltage (50V)

= Year

= Week

= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

SYMBOL	Millimeters			
	Min.	Max.		
A	2.97	3.17		
В	5.70	5.90		
С	2.32	2.52		
d	1.40	1.60		
E	1.40	1.60		
F	5.60	5.70		
Р	3.90	4.10		
P0	3.90	4.10		
P1	1.90	2.10		
Т	0.25	0.35		
W	11.80	12.20		

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